

MOSFETs Silicon N-channel MOS (U-MOSVIII-H)

# TK7S10N1Z

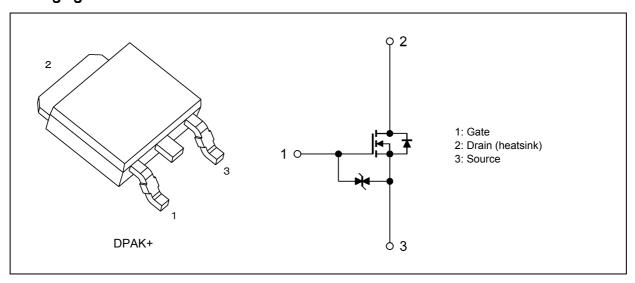
#### 1. Applications

- Automotive
- · Switching Voltage Regulators
- · Motor Drivers

#### 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 40 \text{ m}\Omega$  (typ.) ( $V_{GS} = 10 \text{ V}$ )
- (2) Low leakage current:  $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 100 \text{ V)}$
- (3) Enhancement mode:  $V_{th}$  = 2.0 to 4.0 V ( $V_{DS}$  = 10 V,  $I_D$  = 0.1 mA)

## 3. Packaging and Internal Circuit



# 4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage		V <sub>DSS</sub>	100	V
Gate-source voltage		V <sub>GSS</sub>	±20	
Drain current (DC)	(Note 1)	I <sub>D</sub>	7	Α
Drain current (pulsed)	(Note 1)	I <sub>DP</sub>	21	
Power dissipation $(T_c = 25^{\circ}C)$		P <sub>D</sub>	45.4	W
Single-pulse avalanche energy	(Note 2)	E <sub>AS</sub>	19.6	mJ
Avalanche current		I <sub>AS</sub>	7	Α
Turn-off dV <sub>DS</sub> /dt ruggedness		dV <sub>DS</sub> /dt	8.4	V/ns
Channel temperature		T <sub>ch</sub>	175	°C
Storage temperature		T <sub>stg</sub>	-55 to 175	]

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production



#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R <sub>th(ch-c)</sub>	3.3	°C/W

Note 1: Ensure that the channel temperature does not exceed 175°C.

Note 2:  $V_{DD}$  = 80 V,  $T_{ch}$  = 25°C (initial), L = 307  $\mu$ H,  $R_{G}$  = 25  $\Omega$ ,  $I_{AS}$  = 7 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



#### 6. Electrical Characteristics

## 6.1. Static Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μА
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V	-	-	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	100			V
Drain-source breakdown voltage (Note 3)	V <sub>(BR)DSX</sub>	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	65		_	
Gate threshold voltage	$V_{th}$	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.1 mA	2.0	-	4.0	
Drain-source on-resistance	R <sub>DS(ON)</sub>	$V_{GS}$ = 10 V, $I_D$ = 3.5 A	_	40	48	mΩ

Note 3: If a reverse bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drain-source breakdown voltage is lowered in this mode.

## 6.2. Dynamic Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	470		pF
Reverse transfer capacitance	C <sub>rss</sub>		_	36	_	
Output capacitance	C <sub>oss</sub>		_	260	_	
Switching time (rise time)	t <sub>r</sub>	See Figure 6.2.1.	_	4.6	_	ns
Switching time (turn-on time)	t <sub>on</sub>		_	12.7	_	
Switching time (fall time)	t <sub>f</sub>		_	6.2	_	
Switching time (turn-off time)	t <sub>off</sub>		_	22.7	_	

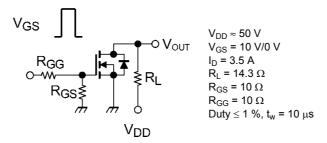


Fig. 6.2.1 Switching Time Test Circuit

## 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	$Q_g$	$V_{DD} \approx 80 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 7 \text{ A}$	_	7.1		nC
Gate-source charge 1	Q <sub>gs1</sub>			3		
Gate-drain charge	$Q_{gd}$		_	2.5		

# 6.4. Source-Drain Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (DC)	(Note 4)	I <sub>DR</sub>	_	_	_	7	Α
Reverse drain current (pulsed)	(Note 4)	I <sub>DRP</sub>		_	_	21	
Diode forward voltage		V <sub>DSF</sub>	I <sub>DR</sub> = 7 A, V <sub>GS</sub> = 0 V	_	_	-1.2	V
Reverse recovery time	(Note 5)	t <sub>rr</sub>	I <sub>DR</sub> = 7 A, V <sub>GS</sub> = 0 V	_	47		ns
Reverse recovery charge	(Note 5)	Q <sub>rr</sub>	-dI <sub>DR</sub> /dt = 50 A/μs	_	28		nC

Note 4: Ensure that the channel temperature does not exceed 175°C.

Note 5: Ensure that V<sub>DS</sub> peak does not exceed V<sub>DSS</sub>.



# 7. Marking (Note)

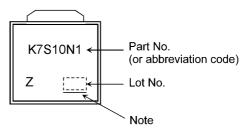


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

### 8. Characteristics Curves (Note)

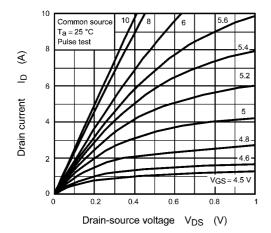


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>

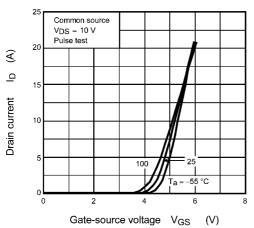


Fig. 8.3 I<sub>D</sub> - V<sub>GS</sub>

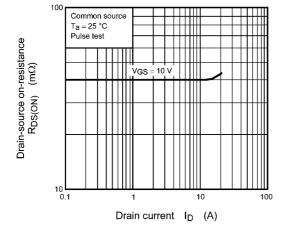


Fig. 8.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

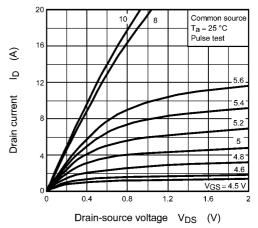


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>

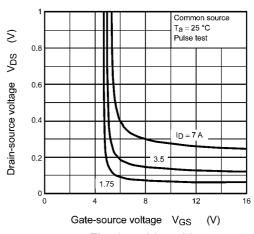


Fig. 8.4 V<sub>DS</sub> - V<sub>GS</sub>

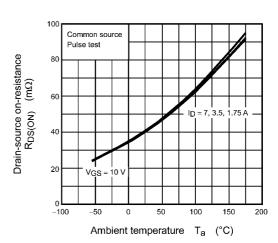


Fig. 8.6 R<sub>DS(ON)</sub> - T<sub>a</sub>

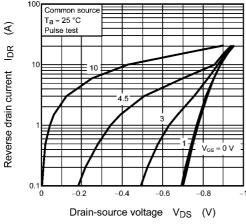


Fig. 8.7  $I_{DR}$  -  $V_{DS}$ 

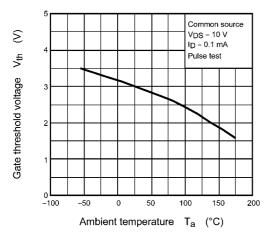


Fig. 8.9 V<sub>th</sub> - T<sub>a</sub>

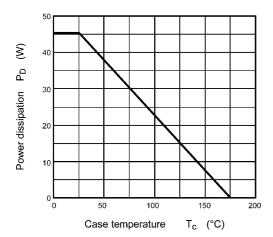


Fig. 8.11 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

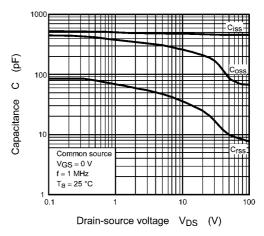


Fig. 8.8 Capacitance - V<sub>DS</sub>

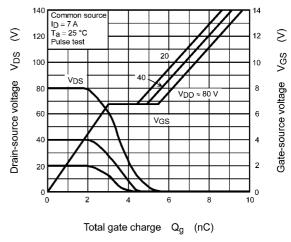


Fig. 8.10 Dynamic Input/Output Characteristics

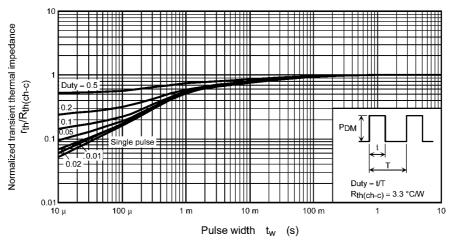


Fig. 8.12  $r_{th}/R_{th(ch-c)} - t_w$  (Guaranteed Maximum)

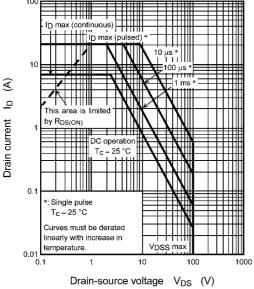


Fig. 8.13 Safe Operating Area (Guaranteed Maximum)

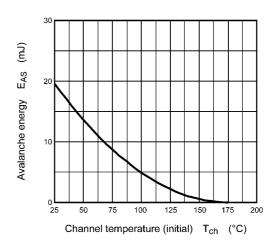


Fig. 8.14 E<sub>AS</sub> - T<sub>ch</sub> (Guaranteed Maximum)

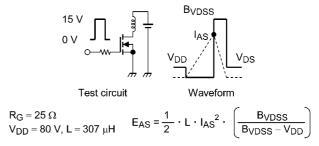


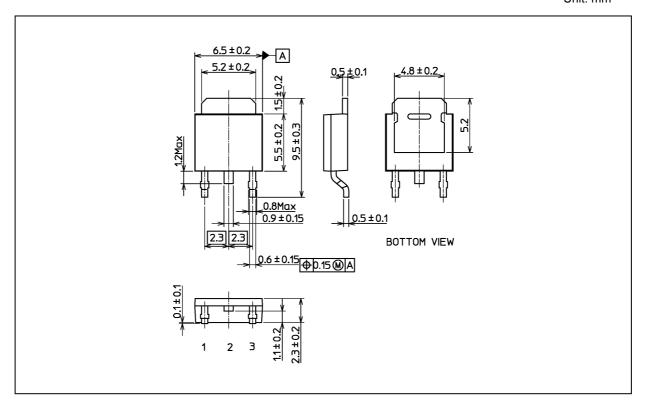
Fig. 8.15 Test Circuit/Waveform

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



# **Package Dimensions**

Unit: mm



Weight: 0.36 g (typ.)

Package Name(s)
TOSHIBA: 2-7M1A
Nickname: DPAK+



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